

PCS CDMA/TDMA 3V POWER AMPL

Typical Applications

- 3V 1850-1910MHz CDMA PCS Handsets
- 3V 1750-1780MHz CDMA PCS Handsets
- 3V TDMA PCS Handsets

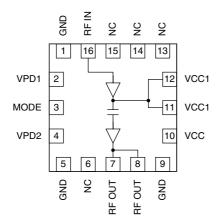
- Spread Spectrum Systems
- Commercial and Consumer Systems
- Portable Battery-Powered Equipment

Product Description

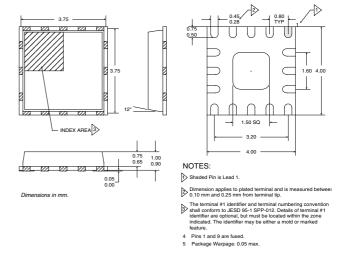
The RF2157 is a high-power, high-efficiency linear amplifier IC targeting 3V handheld systems. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in dual-mode 3V CDMA and TDMA hand-held digital equipment, spread spectrum systems, and other applications in the 1710MHz to 1910MHz band. The device is packaged in a compact 4mmx4mm LCC, as well as a 4mmx4mm MLF (micro leaded package). The frequency response can be optimized for linear performance over 1710MHz to 1910MHz. The device features a digital mode switch which can be used to minimize operating current under low output power conditions.

Optimum Technology Matching® Applied

Si BJT **√** GaAs HBT GaAs MESFET Si Bi-CMOS SiGe HBT Si CMOS



Functional Block Diagram



Package Style: MLF16

Features

- Single 3V Supply
- 29dBm Linear Output Power
- 24dB Linear Gain
- 35% Linear Efficiency
- On-board Power Down Mode
- 1750MHz to 1910MHz Operation

Ordering Information

RF2157 PCS CDMA Power Amplifier RF2157 PCBA Fully Assembled Evaluation Board

RF Micro Devices. Inc. 7625 Thorndike Road Greensboro, NC 27409, USA

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RF2157

Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage (RF off)	+8.0	V_{DC}
Supply Voltage (P _{OUT} ≤31dBm)	+4.5	V_{DC}
Mode Voltage (V _{MODE})	+3.5	V_{DC}
Control Voltage (V _{PD})	+3.5	V_{DC}
Input RF Power	+12	dBm
Operating Case Temperature	-30 to +110	℃
Storage Temperature	-65 to +150	°C



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Devemeter	Specification		11	O andition		
Parameter	Min.	Тур.	Max.	Unit	Condition	
Overall					T=25 °C, V _{CC} =3.4 V, V _{PD} =2.8 V,	
Overall					V _{MODE} ≤0.5V unless otherwise specified	
Usable Frequency Range	1750		1910	MHz		
Typical Frequency Range		1750-1780 1850-1910		MHz MHz	Tuned Matching Network Tuned Matching Network	
Linear Gain	23	25	28	dB	P _{OUT} =29dBm, V _{MODE} ≤0.5V	
	22	24	26	dB	P _{OUT} =29dBm, V _{MODE} ≥2.5V	
Small Signal Gain	24	27	29	dB	P _{IN} ≤-20dBm	
Second Harmonic (Including second harmonic trap)		-35		dBc	IIV	
Third Harmonic		-40		dBc		
Fourth Harmonic		-45		dBc		
Linear Output Power (CDMA/ TDMA Modulation)	29			dBm	V _{MODE} ≤0.5V	
CDMA Linear Efficiency	30	35		%	P _{OUT} =29dBm	
CDMA ACPR @ 1.25MHz		-46	-44	dBc		
Noise Power @ 80MHz Offset		-139		dBm/Hz		
Linear Output Power (CDMA/ TDMA Modulation)	29			dBm	V _{MODE} ≥2.5V	
CDMA Linear Efficiency	33	37		%	P _{OUT} =29dBm	
		6		%	P _{OUT} =16dBm, V _{MODE} ≥2.5V	
CDMA ACPR @ 1.25MHz		-46	-44	dBc	P _{OUT} =29dBm	
Noise Power @ 80MHz Offset		-139		dBm/Hz	P _{OUT} =29dBm	
TDMA Linear Efficiency	30	37		%	P _{OUT} =29dBm	
TDMA ACPR (30kHz Offset)		-31	-28	dBc	P _{OUT} =29dBm	
TDMA ACPR (60kHz Offset)		-52	-48	dBc	P _{OUT} =29dBm	
Linear Output Power (CDMA Modulation)	28			dBm	V _{CC} =3.0V	
Input VSWR		< 2:1				
Output Load VSWR			10:1		No damage.	
Stability	5:1					
Junction to Case Thermal Resistance		25		°C/W		

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Parameter	Specification		المال	Condition	
	Min.	Тур.	Max.	Unit	Condition
Power Supply					
Power Supply Voltage		3.4	4.5	V	
Idle Current		325		mA	V _{MODE} ≤0.5V
	110	140	175	mA	V _{MODE} =2.8V
V _{PD} Current		10		mA	V _{PD} =2.8V
Turn On/Off time			100	ns	
Total Current (Power down)			10	μΑ	V _{PD} ≤0.2dBm
V _{PD} Low Voltage		0	0.2	V	
V _{PD} High Voltage	2.7	2.8	2.9	V	
MODE High Voltage	2.5	2.8			$R_1=1k\Omega$
MODE Low Voltage		0	0.5		

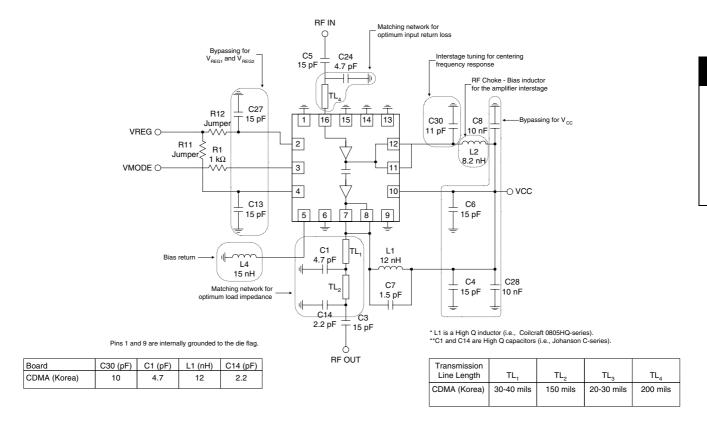
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RF2157

Pin	Function	Description	Interface Schematic
1	GND	This pin is internally grounded to the die flag.	
2	VPD1	Power Down control for first stage. When this pin is "low", first stage circuits are shut off. When this pin is 2.8V, all first stage circuits are operating normally. V _{PD1} requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to pro-	
	MODE	vide the required 2.8 V.	
3	MODE	For full power operation, VMODE is set low. VMODE will reduce the bias current by approximately 50% when set HIGH. Large Signal Gain is reduced approximately 1.5dB at 29dBm P _{OUT} . Small Signal Gain is reduced by approximately 6dB at lower temperatures. An external series resistor is optional to limit the amount of current required.	
4	VPD2	Power Down control for the second stage. When this pin is "low", the second stage circuit is shut off. When this pin is 2.8 V, the second stage circuit is operating normally. V_{PD} requires a regulated 2.8 V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8 V. A 15pF high frequency bypass capacitor is recommended.	
5	GND	Connect to ground plane via 15nH inductor. DC return for the second stage bias circuit.	
6	NC	It is recommended that this pin be connected to the ground plane. This should be isolated from the backside ground contact on the top metal layer.	
7	RF OUT	RF output and power supply for final stage. This is the unmatched collector output of the second stage. A DC block is required following the matching components. The biasing may be provided via a parallel L-C set for resonance at the operating frequency of 1710MHz to 1910MHz. It is important to select an inductor with very low DC resistance with a 1 A current rating. Alternatively, shunt microstrip techniques are also applicable and provide very low DC resistance. Low frequency bypassing is required for stability.	RF OUT From Bias Network
8	RF OUT	Same as pin 7.	See pin 7.
9	GND	This pin is internally grounded to the die flag.	
10	VCC	Supply for bias reference and control circuits. High frequency bypassing may be necessary.	
11	VCC1	Power supply for first stage and interstage match. Pins 11 and 12 should be connected by a common trace where the pins contact the printed circuit board.	
12	VCC1	Same as pin 11.	
13	NC	It is recommended that these pins be connected to the ground plane for improved isolation between RF IN (pin 16) and the VCC1 pins (pins 11 and 12).	
14	NC	It is recommended that these pins be connected to the ground plane for improved isolation between RF IN (pin 16) and the VCC1 pins (pins 11 and 12).	
15	NC	It is recommended that these pins be connected to the ground plane for improved isolation between RF IN (pin 16) and the VCC1 pins (pins 11 and 12).	
16	RF IN	RF input. An external 15pF series capacitor is required as a DC block. In addition, a series transmission line and shunt capacitor, 5pF, are required to provide 2:1 VSWR.	RF IN O From GND1 Stages
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

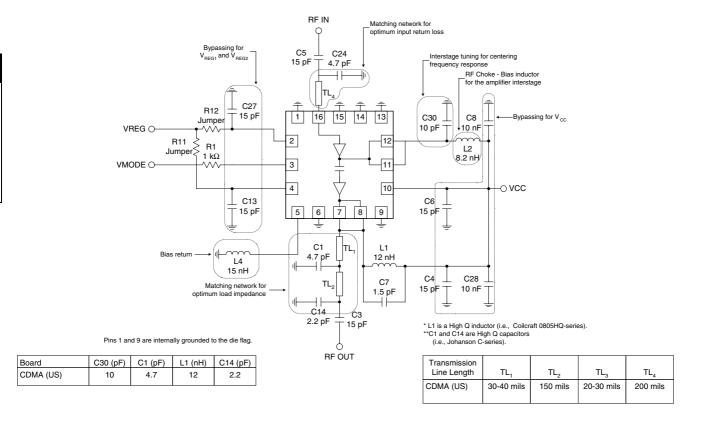
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Application Schematic Korea - CDMA



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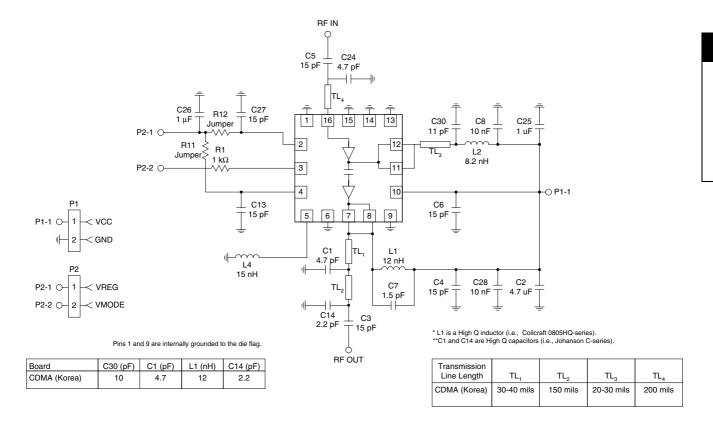
Application Schematic US - CDMA



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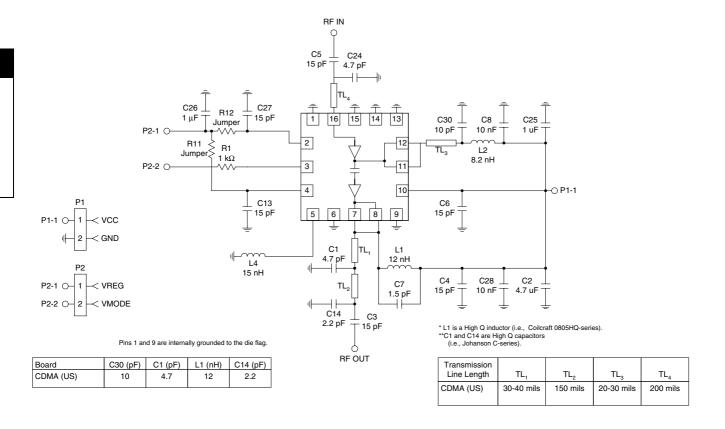
Evaluation Board Schematic Korea - CDMA

(Download Bill of Materials from www.rfmd.com.)



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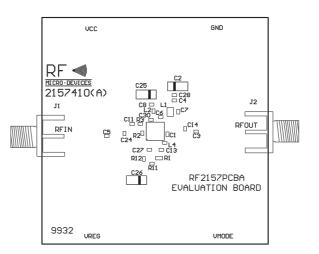
Evaluation Board Schematic US - CDMA

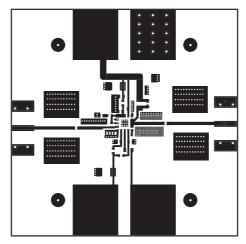


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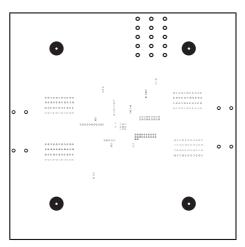
Evaluation Board Layout Board Size 2" x 2"

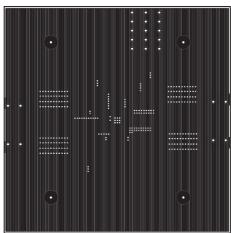
Board Thickness 0.031", Board Material FR-4, Multi-Layer





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